

FORM PTO 1390 (REV 5-93) US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE TRANSMITTAL LETTER TO THE UNITED STATES DESIGNATED/ELECTED OFFICE (DO/EO/US) CONCERNING A FILING UNDER 35 U.S.C. §371		ATTORNEY DOCKET NUMBER 2001_1739A
		U.S. APPLICATION NO. (if known, see 37 CFR 1.57) 09/979505 NEW
International Application No. PCT/JP00/03264	International Filing Date May 22, 2000	Priority Date Claimed May 22, 1999
Title of Invention METHOD AND APPARATUS FOR GROWING HIGH QUALITY SINGLE CRYSTAL		
Applicant(s) For DO/EO/US Takatomo SASAKI et al.		
<p>Applicant herewith submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:</p> <ol style="list-style-type: none"> <input checked="" type="checkbox"/> This is a FIRST submission of items concerning a filing under 35 U.S.C. §371. <input type="checkbox"/> This is a SECOND or SUBSEQUENT submission of items concerning a filing under 35 U.S.C. §371. <input checked="" type="checkbox"/> This express request to begin national examination procedures (35 U.S.C. §371(f)) at any time rather than delay examination until the expiration of the applicable time limit set in 35 U.S.C. §371(b) and PCT Articles 22 and 39(1). <input checked="" type="checkbox"/> A proper Demand for International Preliminary Examination was made by the 19th month from the earliest claimed priority date. <input checked="" type="checkbox"/> A copy of the International Application as filed (35 U.S.C. §371(c)(2)) <ol style="list-style-type: none"> <input type="checkbox"/> is transmitted herewith (required only if not transmitted by the International Bureau). <input checked="" type="checkbox"/> has been transmitted by the International Bureau. ATTACHMENT A <input type="checkbox"/> is not required, as the application was filed in the United States Receiving Office (RO/US) <input checked="" type="checkbox"/> A translation of the International Application into English (35 U.S.C. §371(c)(2)). ATTACHMENT B <input type="checkbox"/> Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. §371(c)(3)). <ol style="list-style-type: none"> <input type="checkbox"/> are transmitted herewith (required only if not transmitted by the International Bureau). <input type="checkbox"/> have been transmitted by the International Bureau. <input type="checkbox"/> have not been made; however, the time limit for making such amendments has NOT expired. <input type="checkbox"/> have not been made and will not be made. <input type="checkbox"/> A translation of the amendments to the claims under PCT Article 19. <input type="checkbox"/> An oath or declaration of the inventor(s) (35 U.S.C. §371(c)(4)). <input checked="" type="checkbox"/> A translation of the annexes to the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. §371(c)(5)). ATTACHMENT C - Please enter these Amended Claims BEFORE entering the Preliminary Amendment of Attachment E <p>Items 11. to 14. below concern other document(s) or information included:</p> <ol style="list-style-type: none"> <input checked="" type="checkbox"/> An Information Disclosure Statement under 37 CFR 1.97 and 1.98. ATTACHMENT D <input type="checkbox"/> An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included. <input checked="" type="checkbox"/> A FIRST preliminary amendment. ATTACHMENT E - Please enter this Preliminary Amendment AFTER entering the Article 34 Amended Claims of Attachment C <ol style="list-style-type: none"> <input type="checkbox"/> A SECOND or SUBSEQUENT preliminary amendment. <input checked="" type="checkbox"/> Other items or information: <ul style="list-style-type: none"> - <u>unexecuted</u> Declaration and Power of Attorney with Cover Letter - ATTACHMENT F 		

U.S. APPLICATION NO. (If known) 09/979505 NEW		INTERNATIONAL APPLICATION NO. PCT/JP00/03264		ATTORNEY'S DOCKET NO. 2001 1739A	
15. [X] The following fees are submitted				CALCULATIONS	PTO USE ONLY
BASIC NATIONAL FEE (37 CFR 1.492(a)(1)-(5)): Neither international preliminary examination fee nor international search fee paid to USPTO and International Search Report not prepared by the EPO or JPO \$1040.00 International Search Report has been prepared by the EPO or JPO \$ 890.00 International preliminary examination fee not paid at USPTO but international search paid to USPTO \$ 740.00 International preliminary examination fee paid to USPTO but claims did not satisfy provisions of PCT Article 33(1)-(4) \$ 690.00 International preliminary examination fee paid to USPTO and all claims satisfied provisions of PCT Article 33(1)-(4) \$ 100.00					
ENTER APPROPRIATE BASIC FEE AMOUNT = \$890.00					
Surcharge of \$130.00 for furnishing the oath or declaration later than [] 20 [] 30 months from the earliest claimed priority date (37 CFR 1.492(e)). \$					
Claims	Number Filed	Number Extra	Rate		
Total Claims	18 - 20 =	0	X \$18.00	\$	
Independent Claims	2 - 3 =	0	X \$84.00	\$	
Multiple dependent claim(s) (if applicable)				+ \$280.00 \$	
TOTAL OF ABOVE CALCULATIONS =				\$890.00	
<input type="checkbox"/> Small Entity Status is hereby asserted. Above fees are reduced by 1/2. \$					
SUBTOTAL = \$890.00					
Processing fee of \$130.00 for furnishing the English translation later than [] 20 [] 30 months from the earliest claimed priority date (37 CFR 1.492(f)). + \$					
TOTAL NATIONAL FEE = \$890.00					
Fee for recording the enclosed assignment (37 CFR 1.21(h)). The assignment must be accompanied by an appropriate cover sheet (37 CFR 3.28, 3.31). \$40 per property + \$					
TOTAL FEES ENCLOSED = \$890.00					
Amount to be refunded \$ Amount to be charged \$					

- a. [X] A check in the amount of \$890.00 to cover the above fees is enclosed. A duplicate copy of this form is enclosed.
- b. Please charge my Deposit Account No. 23-0975 in the amount of \$ _____ to cover the above fees.
A duplicate copy of this sheet is enclosed.
- c. [X] The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any
overpayment to Deposit Account No. 23-0975.

NOTE: Where an appropriate time limit under 37 CFR 1.494 or 1.495 has not been met, a petition to revive (37 CFR 1.137(a) or (b)) must be filed and granted to restore the application to pending status.

19. CORRESPONDENCE ADDRESS



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November 23, 2001

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[2001_1739A]

09/979505

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Takatomo SASAKI et al.

Attn: **BOX PCT**

Serial No. NEW

Docket No. 2001_1739A

Filed November 23, 2001

METHOD AND APPARATUS FOR GROWING
HIGH QUALITY SINGLE CRYSTALTHE COMMISSIONER IS AUTHORIZED
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ACCOUNT NO. 23-0975

[Corresponding to PCT/JP00/03264

Filed May 22, 2000]

ARTICLE 34 AMENDMENTSAssistant Commissioner for Patents,
Washington, DC 20231

Sir:

Kindly enter the attached amended claims prior to initial examination. These amended claims should be entered BEFORE entering the Preliminary Amendment of Attachment E.

Respectfully submitted,

Takatomo SASAKI et al.

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November 23, 2001

Version with Markings to
Show Changes Made

CLAIMS

1. (Delete)
2. (Delete)
- 5 3. (Amended) A method for growing a single crystal comprising arranging a blade member or a baffle member in a raw material melt in a crucible and growing a single crystal by rotating the crucible without rotating the blade member or the baffle member when growing the single crystal by bringing a seed crystal into contact with the raw material melt which is heated and melted within a crucible, wherein the crystal is grown by slowly cooling the raw material melt with which the seed crystal makes contact below liquid level to precipitate a single crystal on the surface of the seed crystal.
- 10 15 4. (Amended) A method according to claim 3, wherein the seed crystal is also rotated while rotating the crucible.
5. (Amended) A method according to claim 3 or 4, wherein a single crystal of an oxide is grown.
- 20 6. A method according to claim 5, wherein the single crystal of an oxide is a single crystal of a borate type oxide.
7. A method according to claim 6, wherein the borate type oxide is $CsLiB_5O_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at least one type among other alkali metal elements and alkali 25 earth metal elements.
8. A method according to claim 7, wherein the oxide is an oxide doped with at least one of Al and Ga elements.

9. A method according to claim 6, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_2$, ($0 < x < 1$) and the crystal is grown by a pulling method.

10. A method according to claim 5, wherein the single 5 crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

11. (Delete)

12. (Delete)

10 13. (Amended) A growing apparatus for growing a single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, comprising a blade member or a baffle member arranged in the raw material melt in the crucible, a rotating material for 15 rotating the crucible and a cooling mechanism for slowly cooling the raw material melt, with which the seed crystal makes contact, below liquid level.

14. (Amended) A growing apparatus according to claim 13 comprising a mechanism for rotating the seed crystal.

20 15. (Amended) An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in claims 13 ~~or 14~~.

16. A growing apparatus according to claim 15 being used for growing a single crystal of a borate type oxide.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Takatomo SASAKI et al.

Attn: BOX PCT

Serial No. NEW

Docket No. 2001_1739A

Filed November 23, 2001

THE COMMISSIONER IS AUTHORIZED
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ACCOUNT NO. 23-0975

METHOD AND APPARATUS FOR GROWING
HIGH QUALITY SINGLE CRYSTAL

[Corresponding to PCT/JP00/03264

Filed May 22, 2000]

PRELIMINARY AMENDMENT TO REDUCE PTO FILING FEE

Assistant Commissioner for Patents,
Washington, DC 20231

Sir:

Please amend the above-identified application as follows.

In the Claims:

Kindly amend claims 5 and 15 as follows.

5. (Amended) A method according to claim 3, wherein a single crystal of an oxide is grown.

15. (Amended) An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in claim 13.

Kindly add new claims 17 and 18 as follows.

17. (New) A method according to claim 4, wherein a single crystal of an oxide is grown.

18. (New) An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in claim 14.

REMARKS

The above claim amendments are presented in order to remove multiple claim dependencies, so as to reduce the required filing fee.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attachment page is captioned "**Version with markings to show changes made.**"

Respectfully submitted,

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71PPTS

METHOD AND APPARATUS FOR GROWING
HIGH QUALITY SINGLE CRYSTAL

TECHNICAL FIELD

5 The present invention relates to a method and an apparatus for growing a high quality single crystal. Particularly, the present invention relates to a new method for growing a high quality single crystal, the method being capable of growing a high quality single crystal using even
10 highly viscous liquid raw materials and to an apparatus for practicing the method.

BACKGROUND ART

Conventionally, as a method for growing a single crystal of an oxide or the like, a method is known in which raw materials are melted under heating in a crucible, thereafter a seed crystal is brought into contact with the raw material melt and a round bar-like single crystal is pulled up with rotating this seed crystal to grow a single crystal. This pulling method
15 is used for the growth of various single crystals as a method which can grow a large-diameter crystal in an efficient manner.

20 Also, for example, a method (Kyropoulos method) is known in which raw materials are melted under heating in a crucible, thereafter a seed crystal is brought into contact with the raw material melt and the temperature below liquid level is slowly lowered to precipitate and grow a crystal.

25 However, in the conventional methods of growing a single

crystal by bringing a seed crystal into contact with a raw material melt, there is the problem that when the viscosity of the raw material melt during growth at the required temperature is high, the flow of the raw material melt in the 5 crucible is retarded, causing nonuniformity in temperature, the degree of supersaturation or the like, leading to the result that the quality of the crystal tends to be lowered.

For example, $\text{CsLiB}_5\text{O}_{10}$ (CLBO) and the like as non-linear optical crystals attract attention as those for the generation 10 of high output ultraviolet laser light and are desired to have excellent performances and qualities such as very high resistance to damages by lasers, very high optical loss and high uniformity. However, since it is a borate type crystal, its melt has a high viscosity, which makes it difficult to 15 grow a high quality and high performance single crystal. It has been confirmed that in actual measurement, the viscosity of a CLBO solution of a self flux composition is as high as about 1000 cs (centistokes) at a growth temperature, around 840°C.

20 For example, in the growth of a single crystal by means of the rotation of a seed bar in the CLBO cooling method, the distribution of temperature in the raw material melt is not good as shown in FIG. 7 and the growth of a crystal is rapid, and therefore there is a restriction inevitably on the growth 25 of a high quality and high performance crystal.

In view of this situation, it is an object of the present invention to solve the problems in prior art as mentioned above

and to provide an improved new method which can grow a high quality and high performance single crystal in the case of using even a highly viscous raw material melt and also to provide an apparatus for practicing the method.

5

DISCLOSURE OF INVENTION

The present invention has been made to solve the aforementioned problem and, first, provides a method for growing a high quality single crystal, comprising growing a 10 single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, wherein a blade member or a baffle member is arranged in the raw material melt in the crucible, and the crystal is grown with rotating the crucible without rotating the blade member 15 or the baffle member. Also, the present invention provides, second the method for growing by slowly pulling up the seed crystal which is brought into contact with the raw material melt, third the method for growing by slowly cooling the raw material melt with which the seed crystal makes contact below 20 liquid level to precipitate a single crystal on the surface of the seed crystal, fourth the method wherein the seed crystal is also rotated while rotating the crucible, fifth said method wherein a single crystal of an oxide is grown, sixth the method wherein the single crystal of an oxide is a single crystal 25 of a borate type oxide, seventh the method wherein the borate type oxide is $CsLiB_5O_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at

least one type among other alkali metal elements and alkali earth metal elements and eighth the method wherein the oxide is an oxide doped with at least one of Al and Ga elements. The present invention provides, ninth, the method wherein the 5 borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_3$ ($0 < x < 1$) and the crystal is grown by a pulling method and tenth the method wherein the single crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

10 Further, the present invention provides, eleventh, an apparatus for growing a high quality single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, comprising a blade member or a baffle member arranged in the raw material melt 15 in the crucible and a rotating material for rotating the crucible, twelfth the growing apparatus comprising a pulling mechanism for slowly pulling up the seed crystal which is brought into contact with the raw material melt, thirteenth the growing apparatus comprising a cooling mechanism for slowly 20 cooling the raw material melt, with which the seed crystal makes contact, below liquid level, fourteenth the apparatus comprising a mechanism for rotating the seed crystal, fifteenth an apparatus for growing a single crystal of an oxide according to any one of the aforementioned growing apparatuses and 25 sixteenth said apparatus for growing a single crystal of a borate type oxide.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a structural view showing the outline of a method and an apparatus according to this invention.

FIG. 2 is a sectional view showing a growing apparatus 5 as an example.

FIG. 3 is a plan view illustrating a blade member.

FIG. 4 is a side view of a blade member.

FIG. 5 is a view showing the hysteresis of crystal growth.

FIG. 6 is a view showing the distribution of temperature 10 in a raw material melt.

FIG. 7 is a view showing the distribution of temperature in a melt in the case of a conventional method.

The symbols in these figures represent the following parts.

15	1 Crucible
	2 Raw material melt
	3 Seed bar
	4 Seed crystal
	5 Blade member
20	6 Rotating member
	7 Support bar

BEST MODE FOR CARRYING OUT THE INVENTION

The present invention has the characteristics as 25 aforementioned and embodiments of the invention will be hereinafter explained.

First, a method for growing a single crystal according

to the present invention is based upon the ground that a seed crystal is brought into contact with a melt of raw materials melted under heating in a crucible to grow a single crystal. In the growing method of this invention, various modes such 5 as a conventionally known pulling method and a cooling method (kyropoulos method) using gradual cooling are optionally adopted. The point that the seed crystal is brought into contact with the melt (including the case of a melt) produced by melting raw materials to grow a single crystal is common 10 by melting raw materials to grow a single crystal is common to all of these modes.

When practicing the method of this invention, a growing apparatus basically comprises a crucible, a heating means for heating and melting raw materials placed in the crucible, a means for detecting and controlling heating temperature and 15 a crystal support means for bringing a seed crystal into contact with a melt (including a melt) of the raw materials which are melted under heating. As shown in FIG. 1 showing the typical view of the apparatus, the present invention has the characteristics that when a seed crystal (4) supported by a 20 crystal support means such as a seed bar (3) is brought into contact with a melt (2) of raw materials melted under heating in a crucible (1) to grow a single crystal, a blade member (5) or a baffle member is disposed in the raw material melt (2) in the crucible (1) and the crucible is rotated to grow the 25 single crystal. For the rotation of the crucible (1), the growing apparatus is provided with a rotating material (6) which rotates the crucible (1) in the condition that the

crucible (1) is mounted thereon.

In the case of a pulling method, the seed bar (3) is pulled up towards above with rotating the seed bar (3) or in such a stationary state that the seed bar (3) is not rotated.

5 On the other hand, in the case of the cooling method, for example, a method in which using a hollow seed bar (3), cooling gas is supplied to the hollow portion and the raw material melt below liquid level is cooled slowly to precipitate a single crystal on the surface of the seed crystal (4), thereby growing 10 a single crystal or a method in which the temperature of whole heaters in a furnace is slowly lowered to cool the temperature of the raw material melt below liquid level may be adopted. The former method is used to prevent the seed crystal from being melted. In these cases, the support means such as the 15 seed bar (3) may also be either rotated or be in such a stationary state that the seed bar (3) is not rotated. It is to be noted that the present invention has, as its basic thought, the characteristics that the rotations of the seed bar (3) as aforementioned and seed crystal (4) which are supported by 20 the seed bar (3) are made to be unessential and the crucible (1) is rotated. Whether the seed bar (3) and the seed crystal (4) are rotated or not is determined properly according to the need as a relative motion to the rotation of the crucible (1).

25 In the present invention, the blade member (5) or the baffle member itself may be in a stationary state whereas the crucible (1) is designed to be rotated by the rotating material

(6) in the raw material melt (2) as shown in, for example.

FIG. 1.

The presence of the blade member (5) or baffle member having such characteristics and the rotation of the crucible 5 (1) enhance the effect of stirring the raw material melt, which makes it possible to make thin the diffusion boundary layer, to increase the amount of the raw materials to be supplied to the growth surface and to make the degree of supersaturation uniform. This enables the growth of a high quality and high 10 performance single crystal even if the raw material melt is highly viscous at the growth temperature.

The blade member (5) or baffle member as those having various shapes may be arranged in consideration of the composition and type of single crystal which is a subject of 15 growth and raw material, the composition and viscosity of the raw material melt, further the depth of the above member inserted into the raw material melt (2), a distance from the rotation center of the crucible (1), the flow direction and flow speed of the raw material melt (2) and the like. As 20 preferable examples of the blade member (5) or baffle member, plural blades are arranged radially and fixed at the center of them. Namely, those made to have a screw form and those obtained by arranging plural baffle plate fragments are exemplified.

25 Although these blade member (5) and baffle member is not rotated but placed in a stationary state, vibrations and motions such as reciprocating motions in at least one of a

vertical direction and a horizontal direction may be imparted to these members. Also, as shown in FIG. 1, the blade member (5) or baffle member may be inserted into the crucible (1) from the above and pulled up by the support bar (7), may be disposed such that, for example, the depth of the member to be arranged in the raw material melt (2) can be adjusted and may be fitted and fixed to the bottom or the like of the crucible (1). More preferably, it is considered to make the member have the former structure.

10 As to the rotation of the crucible (1) by means of the rotating material (6), it is considered that the crucible (1) is made to be able to rotate in a direction positive with respect to the direction of the rotation of the seed crystal (4) or in both directions reversely. Also, regarding the rotation 15 of the crucible (1), it is considered to change the rate of rotation under control during the course of the growth. It is also considered that the direction of rotation and the rate of rotation are changed under control in relation to optical detection of, for example, the flow and temperature of the 20 melt and growth size of the single crystal or to pressure sensitive and heat-sensitive detection of, for example, the flow and temperature of the melt at the blade member (5) or the support bar (7) in the crucible (1).

The single crystal which is an object of this invention 25 may be various types and this invention is more effective when the raw material melt is highly viscous at growth temperatures. As examples of the single crystal, various oxides are given.

Particularly, this invention is suitable for the growth of highly viscous borate type crystals such as $CsLiB_5O_10$ (CLBO) for which a high quality and high performance single crystal is expected, compositions prepared by partially substituting 5 at least one of Cs and Li of $CsLiB_5O_10$ with one of other alkali metal elements or alkali earth metal atoms or those doped with an atom such as Al or Ga. In an example explained later, explanations are offered taking, as an example, the case where the above CLBO is grown by a cooling method, though the invention 10 is not limited to this case.

Also in the growth of a crystal of GdYCOB, namely, $Gd_xY_{1-x}Ca_4O(BO_3)$, by a pulling method (Czochralski method: Cz method), a high quality crystal is obtained by the method of this invention. In the pulling method in particular, it is 15 also effective to dispose the baffle member.

Also, as the oxides to be grown, $LiNbO_3$, $LiTaO_3$, high-temperature superconductive oxide materials and heat-electricity conversion oxide materials such as $Na_xCO_2O_4$ (x is about 1) are also exemplified.

20 Now, the present invention will be explained in more detail by way of examples shown below.

EXAMPLES

(Growing apparatus)

25 As a growing apparatus, the whole was designed to have the structure of FIG. 2. Using a platinum crucible, the crucible was designed to be able to be rotated by a motor.

Also, in this apparatus, a hollow one was used as a seed bar (3), a seed crystal (4) was supported by the lower end of the seed bar (3) and the seed crystal (4) was designed to be capable of being cooled by supplying seed-cooling gas to the inside 5 of the hollow seed bar (3). This prevented the seed crystal (4) from melting and falling. This apparatus enables growth using a melt composition which conventionally involves a difficulty in the growth of a crystal because the seed crystal melts.

10 In the platinum crucible, a screw type blade member (5) made of platinum shown in FIG. 3 and FIG. 4 was disposed by fitting it to the support bar (7). The blade member (5) had six blades which were arranged at a blade angle of 40 degrees. The blade member (5) was arranged such that the center (A) 15 of the blade was disposed at a plane position corresponding to the center of rotation of the crucible. The distance (H) from the inside bottom of the crucible to the center (A) of the blade was designed to be capable of being controlled. It is to be noted that as to the distance (H), the center (A) 20 of the blade was designed to be positioned as close as possible to the inside bottom of the crucible.

It is to be noted that both of the Alsynto pipe and FKS pipe shown in FIG. 4 were purchased from FURUYAMETAL CO., LTD.). The Alsynto pipe was made of alumina (Al_2O_3) as its primary 25 raw material and the FKS pipe was constituted of a material comprising platinum (Pt) containing ZrO_2 .

(Single crystal growth)

Using the aforementioned growing apparatus, the crucible was rotated to grow a CLBO single crystal by a cooling method.

The seed bar was not rotated and similarly the blade member was not rotated to make growth in a stationary state. The raw material melt was made to have a CLBO self flux composition. The percentage composition of this self flux was as follows: Cs : Li : B : O = 1 : 1 : 5.5 : 9.2. Also, it has been confirmed that this composition is preferably a stoichiometric composition (melt composition).

The maximum heating temperature of the raw material melt was set to 900°C.

Each condition of temperature descending rate and the rotation of the crucible was as follows.

15 Temperature descending rate

0.1°C/day

Rotation of the crucible

30 rpm

The position where the temperature descending rate was measured was the level of the melt as the first standard. Thereafter, the temperature of the melt was made to descend at a rate of 0.1°C/day from the temperature at the level. The temperature at this time was measured by control sensors shown in FIG. 2 and the temperature of the whole melt was made to descend equally at a rate of 0.1°C/day.

FIG. 5 shows the hysteresis of the crystal when compared with that of a conventional usual method and FIG. 6 shows the

distribution of temperature in the raw material melt. It is understood from FIG. 6 that the distribution of temperature of the melt in the crucible is made more uniform in the direction of the height than that of a conventional method and the crystal 5 is grown uniformly.

Further studies as to the results of the distribution of temperature in the raw material melt in FIG. 6 proved it desirable for the growth of a high quality crystal that a difference (Δt) in temperature between positions extending 10 from the liquid level up to a height (depth) of about 10 cm was in a range of up to -0.5°C , namely between -0.5°C to 0°C .

Also, as shown in FIG. 5, in the conventional growing method, although a growth at the first start is slow, the rate of growth rises on the way and the final rate of growth becomes 15 considerably high. This shows that when a crystal is small, a poor stirring effect is produced even if a seed bar is rotated whereas when a crystal is large, the crystal itself stirs a melt to thereby accelerate the growth instantly.

On the contrary, in the growth according to the method 20 of this invention in which the blade member is inserted and the crucible is rotated, a growth at the first start is faster than in the case of the conventional growth using the rotation of a seedbar. This is because the melt is sufficiently stirred by the rotation of the crucible and therefore a layer called 25 the diffusion boundary layer which determines the rate of growth becomes thin. Further, this is because the degree of supersaturation is made uniform.

(Evaluation of crystals)

In order to evaluate the quality of the grown crystal, samples prepared by cutting the crystal into wafer-like shapes 1.5 cm in thickness and polishing the three-planes of the cut 5 crystal were subjected to a test using a He-Ne laser to observe the internal diffusion in the crystal. In the crystals having high qualities, diffusion arises in the inside and the inside is bright with red light, so that the points of diffusion were seen. In deficient places, passes were viewed.

10 As a result of the observation, it was confirmed that the crystal grown according to the method of this invention in which the blade member was inserted and the crucible was rotated had good qualities and a few passes were viewed at the lower portion of the seed crystal.

15 On the other hand, in the crystals grown by the conventional method, passes were viewed as a whole, giving rise to a problem concerning the qualities of the crystal.

Also, as samples for the evaluation of resistance to a laser, the same samples as above and crystals 10 mm×10 mm 20 ×15 mm in size which were grown by the conventional method were used. The measurement of damage threshold value was made for the (001) plane. As the laser light source, a longitudinal and lateral single mode Q switch Nd:YAG laser was used. The evaluation was made using an oscillation wavelength of 266 25 nm which was fourth harmonics of the Nd:YAG laser. The pulse width was 0.75 ns.

Light having a diameter of 8 mm was converged using a

lens with a focal distance of 100 mm. Here, the position of the crystal was adjusted such that the focus portion was located at a distance of 5 mm from the plane of incidence and the crystal was moved every shot. It has been confirmed that no damage is produced on the plane of incidence in the light conversion condition in this case. Continuous light of a He-Ne laser was allowed to pass on the same axis of the Nd:YAG laser to confirm whether a diffusion point was present or not on the portion irradiated with the laser light every movement and to examine visually whether or not diffusion points newly occurred after the shot to thereby determine whether damages were present or not. When the incident energy is higher than the damage threshold value, plasma was observed at the light convergence portion. In the vicinity of the threshold value, the occurrence of diffusion points was only confirmed. The intensity of the laser pulse was changed by a combination of a $\lambda/2$ plate (polarization rotor) and a polarizer. The incident energy was monitored by a biplanaphoto tube and an oscilloscope which were calibrated by a calorimeter. Fused quartz (10.4 GW/cm^2) was used as a reference example.

The internal laser damage threshold value was measured using the fourth harmonics (266 nm) of an Nd:YAG laser in such procedures. The internal laser damage threshold value of the crystal grown according to this invention in which the blade member was inserted and the crucible was rotated and the internal laser damage threshold values of the crystal grown by the conventional method and fused quartz are shown in Table

1.

Table 1

Method	Damage threshold value (GW/cm ²)
Fused quartz	10.4
Conventional method	8.8-8.9
This invention	10.4-20.8

5

As shown in Table 1, it was confirmed that the internal laser damage threshold value of the crystal grown by the conventional growing method was lower than that of fused quartz whereas the internal laser damage threshold value of the 10 crystal grown according to the method of this invention in which the blade member was inserted and the crucible was rotated was higher than that of fused quartz even when the threshold value was lower and was about two times that of fused quartz when the threshold value was the highest.

15 As mentioned above, when comparing the internal laser damage threshold value of the crystal grown by the conventional method with that of the crystal grown by the method of this invention, it is understood that the crystal of this invention is considerably higher than the conventional crystal in the 20 internal laser damage threshold value. This means that the crystallinity is significantly improved.

INDUSTRIAL APPLICABILITY

As mentioned above in detail, the present invention

ensures that various single crystals including CLBO are grown as high quality and high performance crystals from a highly viscous raw material melt.

CLAIMS

1. A method for growing a high quality single crystal comprising growing a single crystal by bringing a seed crystal 5 into contact with a raw material melt which is heated and melted within a crucible, wherein a blade member or a baffle member is arranged in the raw material melt in the crucible, and the crystal is grown with rotating the crucible without rotating the blade member or the baffle member.

10 2. A method according to claim 1, wherein the single crystal is grown by slowly pulling up the seed crystal which is brought into contact with the raw material melt.

15 3. A method according to claim 1, wherein the crystal is grown by slowly cooling the raw material melt with which the seed crystal makes contact below liquid level to precipitate a single crystal on the surface of the seed crystal.

4. A method according to anyone of claims 1 to 3, wherein the seed crystal is also rotated while rotating the crucible.

5. A method according to anyone of claims 1 to 4, wherein 20 a single crystal of an oxide is grown.

6. A method according to claim 5, wherein the single crystal of an oxide is a single crystal of a borate type oxide.

7. A method according to claim 6, wherein the borate type oxide is $CsLiB_5O_{10}$ or an oxide obtained by partially 25 substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at least one type among other alkali metal elements and alkali earth metal elements.

8. A method according to claim 7, wherein the oxide is an oxide doped with at least one of Al and Ga elements.

9. A method according to claim 6, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_3$ ($0 < x < 1$) and the 5 crystal is grown by a pulling method.

10. A method according to claim 5, wherein the single crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

10 11. An apparatus for growing a high quality single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, comprising a blade member or a baffle member arranged in the raw material melt in the crucible and a rotating material for 15 rotating the crucible.

12. A growing apparatus according to claim 11 comprising a pulling mechanism for slowly pulling up the seed crystal which is brought into contact with the raw material melt.

20 13. A growing apparatus according to claim 11 comprising a cooling mechanism for slowly cooling the raw material melt, with which the seed crystal makes contact, below liquid level.

25 14. A growing apparatus according to any one of claims 11 to 13 comprising a mechanism for rotating the seed crystal.

15. An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in any one

of claims 11 to 14.

16. A growing apparatus according to claim 15 being used for growing a single crystal of a borate type oxide.

CLAIMS

1. (Delete)
2. (Delete)
- 5 3. (Amended) A method for growing a single crystal comprising arranging a blade member or a baffle member in a raw material melt in a crucible and growing a single crystal by rotating the crucible without rotating the blade member or the baffle member when growing the single crystal by bringing a seed crystal into contact with the raw material melt which is heated and melted within a crucible, wherein the crystal is grown by slowly cooling the raw material melt with which the seed crystal makes contact below liquid level to precipitate a single crystal on the surface of the seed crystal.
- 10 4. (Amended) A method according to claim 3, wherein the seed crystal is also rotated while rotating the crucible.
- 15 5. (Amended) A method according to claims 3 or 4, wherein a single crystal of an oxide is grown.
- 20 6. A method according to claim 5, wherein the single crystal of an oxide is a single crystal of a borate type oxide.
- 25 7. A method according to claim 6, wherein the borate type oxide is $CsLiB_5O_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $CsLiB_5O_{10}$ with at least one type among other alkali metal elements and alkali earth metal elements.
8. A method according to claim 7, wherein the oxide is an oxide doped with at least one of Al and Ga elements.

9. A method according to claim 6, wherein the borate type oxide is represented by $Gd_xY_{1-x}Ca_4O(BO_3)_x$, ($0 < x < 1$) and the crystal is grown by a pulling method.

10. A method according to claim 5, wherein the single 5 crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

11. (Delete)

12. (Delete)

10 13. (Amended) A growing apparatus for growing a single crystal by bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible, comprising a blade member or a baffle member arranged in the raw material melt in the crucible, a rotating material for 15 rotating the crucible and a cooling mechanism for slowly cooling the raw material melt, with which the seed crystal makes contact, below liquid level.

14. (Amended) A growing apparatus according to claim 13 comprising a mechanism for rotating the seed crystal.

20 15. (Amended) An apparatus for growing a single crystal of an oxide comprising the growing apparatus as claimed in claims 13 or 14.

16. A growing apparatus according to claim 15 being used for growing a single crystal of a borate type oxide.

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Fig.1

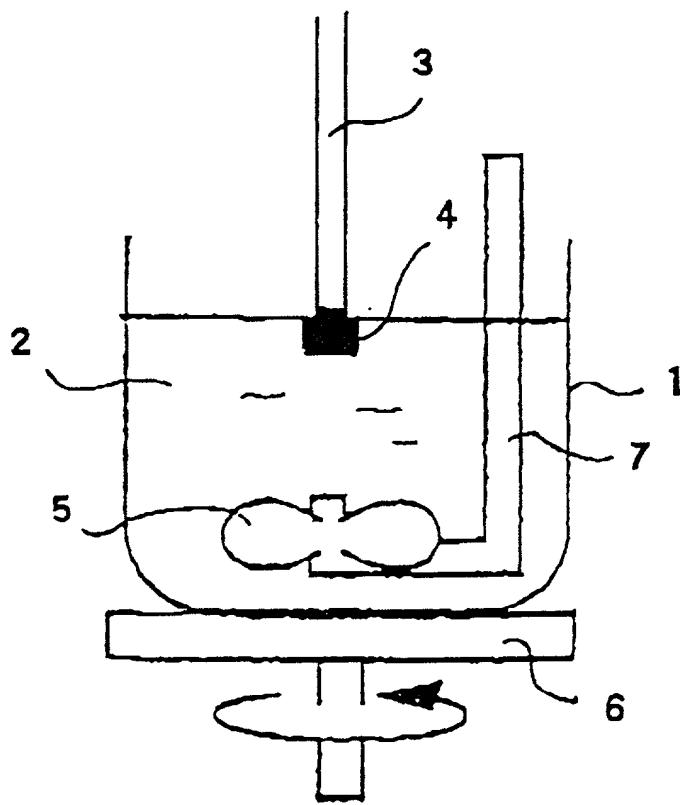


Fig.2

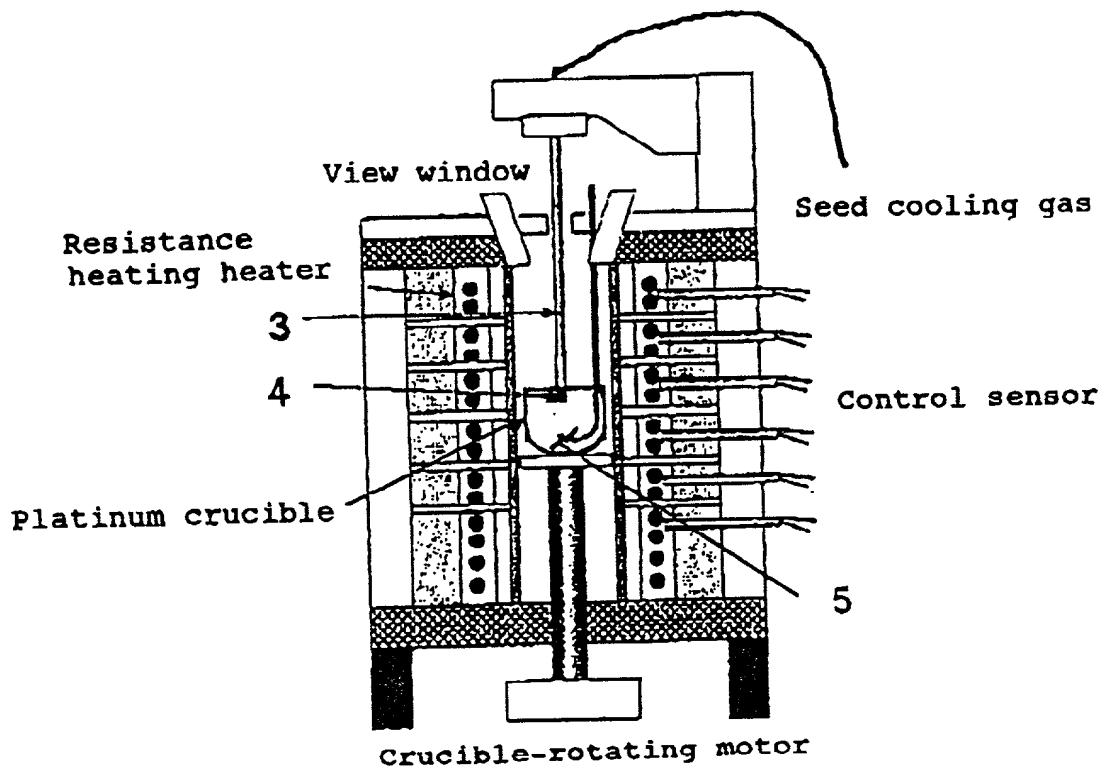
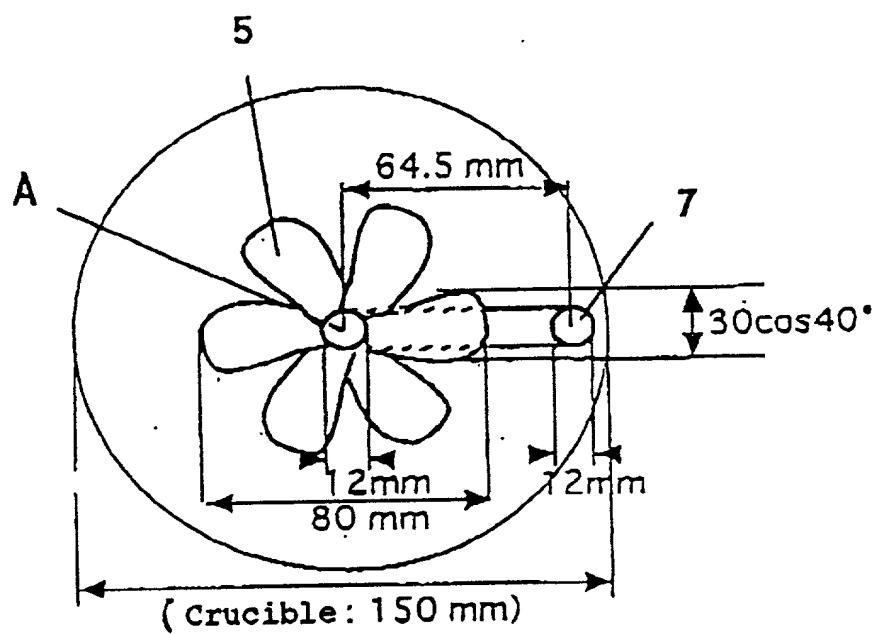
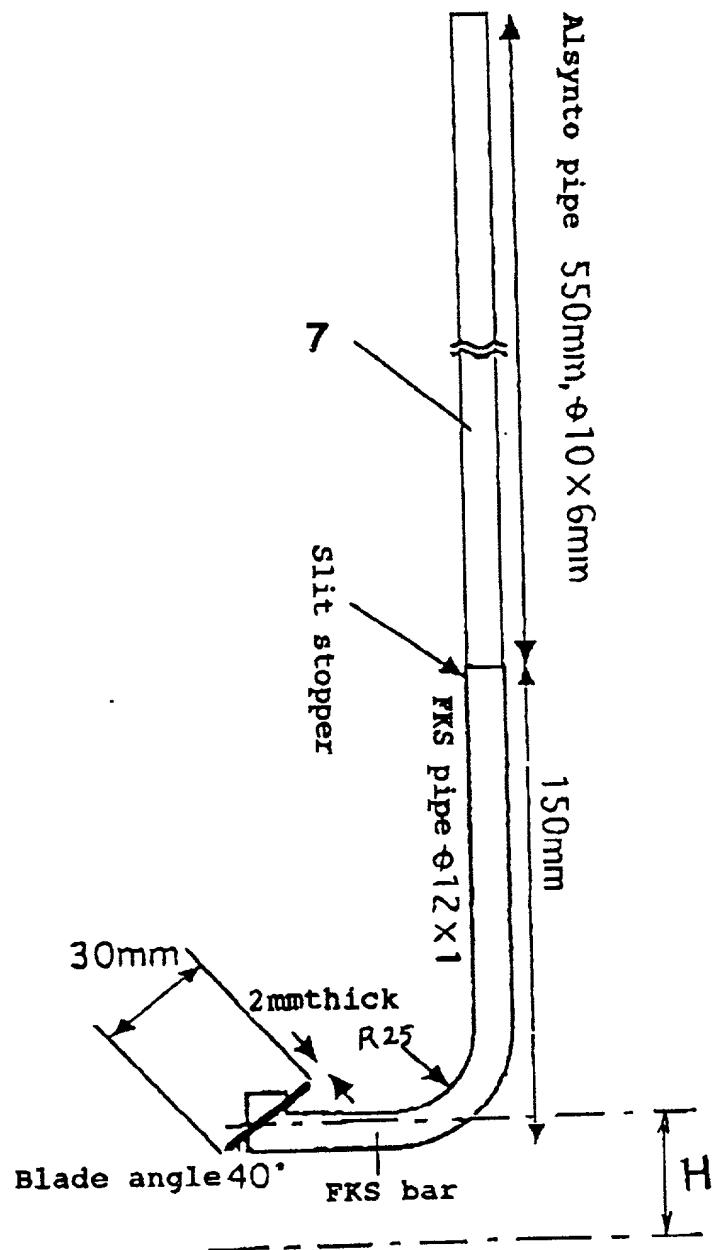


Fig.3



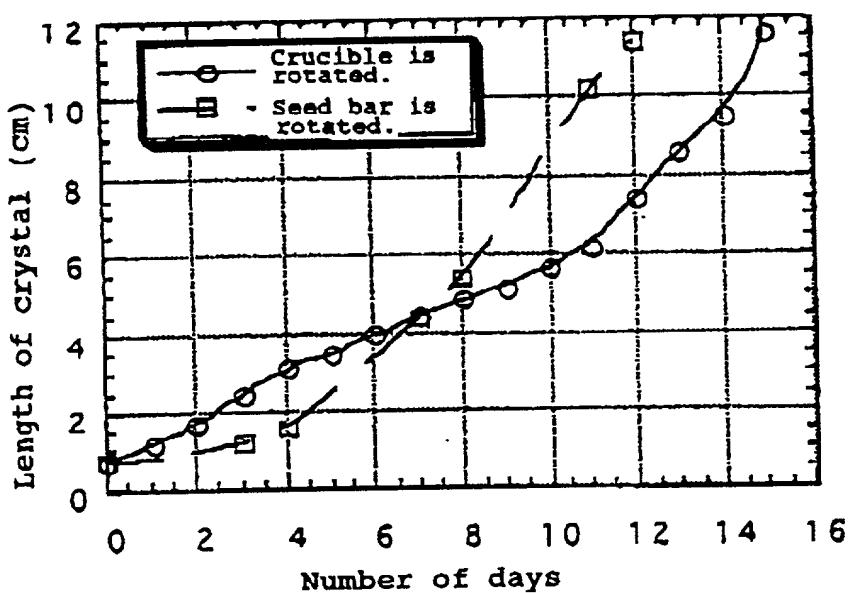
09/979505

Fig.4



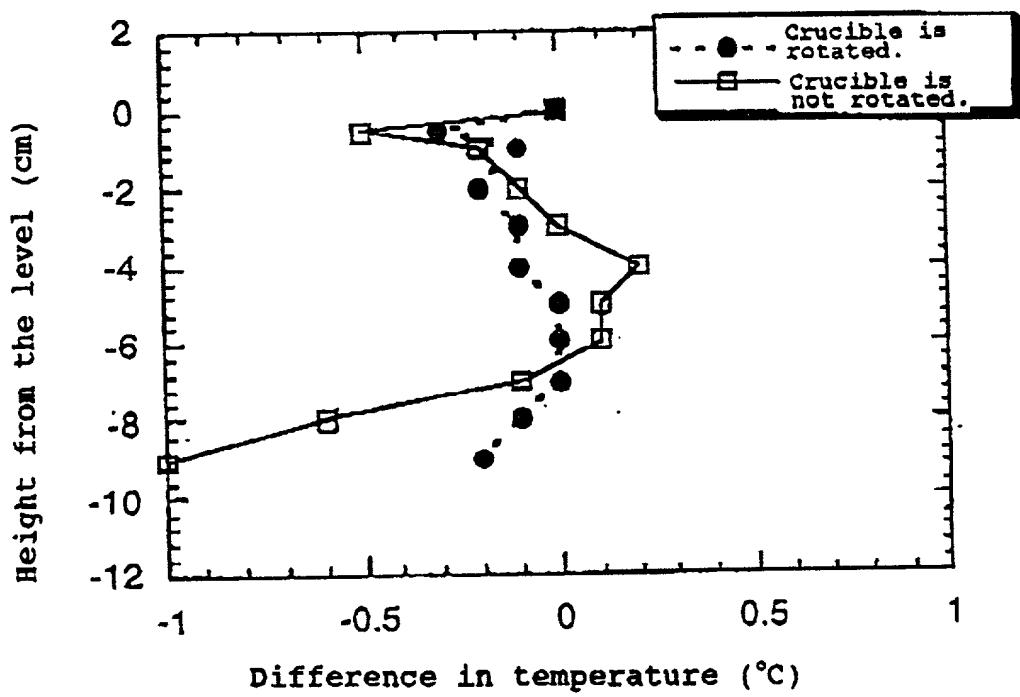
09/979505

Fig.5



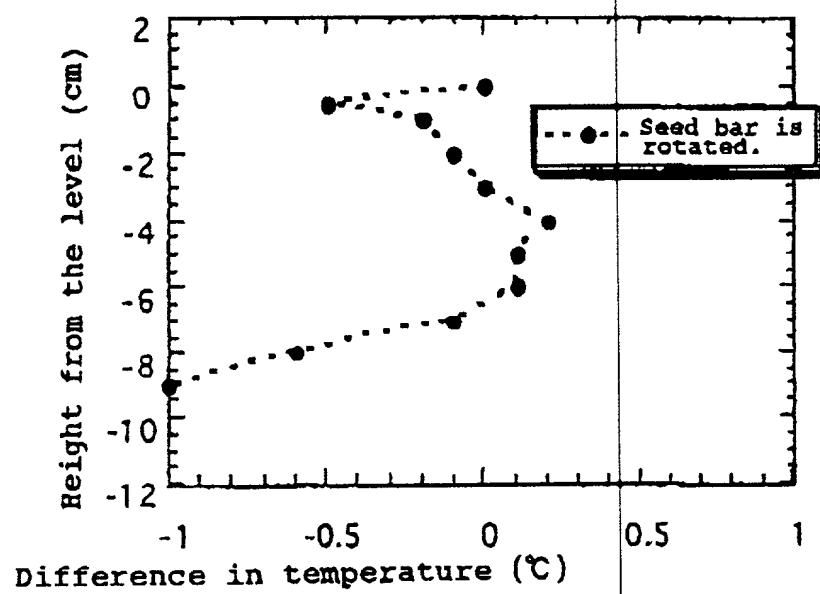
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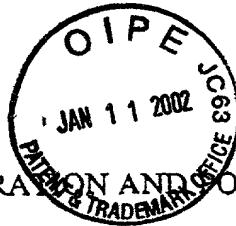
Fig.6



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Fig. 7





09/9/2002

DECLARATION AND POWER OF ATTORNEY FOR U.S. PATENT APPLICATION

() Original () Supplemental () Substitute (X) PCT () DESIGN

As a below named inventor, I hereby declare that: my residence, post office address and citizenship are as stated below next to my name; that I verily believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural inventors are named below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

Title: METHOD AND APPARATUS FOR GROWING HIGH QUALITY SINGLE CRYSTAL

of which is described and claimed in:

() the attached specification, or
 () the specification in application Serial No. _____, filed _____, and with amendments
 through _____, or
 (X) the specification in International Application No. PCT/JP00/03264, filed May 22, 2000, and as amended on _____
 (if applicable).

I hereby state that I have reviewed and understand the content of the above-identified specification, including the claims, as amended by any amendment(s) referred to above.

I acknowledge my duty to disclose to the Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56.

I hereby claim priority benefits under Title 35, United States Code, §119 (and §172 if this application is for a Design) of any application(s) for patent or inventor's certificate listed below and have also identified below any application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

COUNTRY	APPLICATION NO.	DATE OF FILING	PRIORITY CLAIMED
Japan	1999-178815	May 22, 1999	YES

I hereby claim the benefit under Title 35, United States Code §120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code §112, I acknowledge the duty to disclose information material to patentability as defined in Title 37, Code of Federal Regulations, §1.56 which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

APPLICATION SERIAL NO.	U.S. FILING DATE	STATUS: PATENTED, PENDING, ABANDONED

And I hereby appoint Michael R. Davis, Reg. No. 25,134; Matthew M. Jacob, Reg. No. 25,154; Warren M. Cheek, Jr., Reg. No. 33,367; Nils Pedersen, Reg. No. 33,145; Charles R. Watts, Reg. No. 33,147; and Michael S. Huppert, Reg. No. 40,268, who together constitute the firm of WENDEROTH, LIND & PONACK, L.L.P., as well as any other attorneys and agents associated with Customer No. 000513, to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected therewith.

I hereby authorize the U.S. attorneys and agents named herein to accept and follow instructions from NISHIZAWA & ASSOCIATES as to any action to be taken in the U.S. Patent and Trademark Office regarding this application without direct communication between the U.S. attorneys and myself. In the event of a change in the persons from whom instructions may be taken, the U.S. attorneys named herein will be so notified by me.

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I further declare that all statements made herein of my own knowledge are true, and that all statements on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

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5th Inventor _____ Date _____
6th Inventor _____ Date _____

The above application may be more particularly identified as follows:

U.S. Application Serial No. _____ Filing Date November 23, 2001

Applicant Reference Number 00-F-024US/UA Atty Docket No. 2001 1739A

Title of Invention METHOD AND APPARATUS FOR GROWING HIGH QUALITY SINGLE CRYSTAL